

Photoelectric Sensor

Photoelectric sensor is a device for converting the optical signal into electrical signal. It has good current linearity, low cost, small volume, long life and other advantages, It is suitable for detecting rapid changing of optical signal, such as light communication, fiber optics, distance measurement, face communication, etc.

• Features

- ▶ Si-based NIP planar type
- ▶ Chip size 60mil * 60mil

• Structure

- ▶ Electrode topside (cathode): Aluminum
- ▶ Electrode backside (anode): Ag

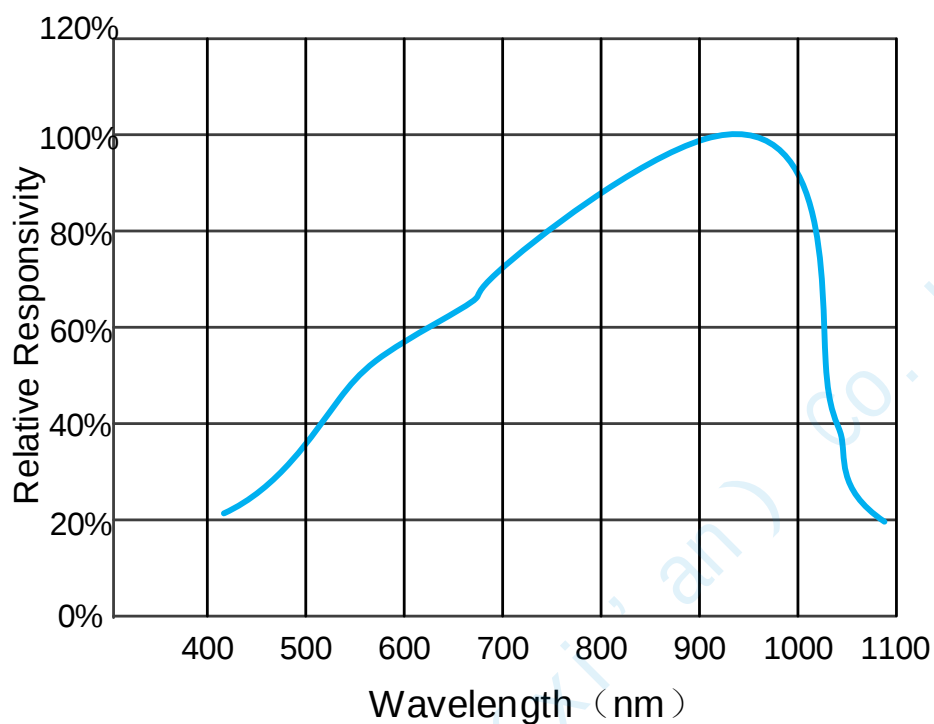
• Size

Parameter	Value (mil)	Value (mm)
Chip size	60mil × 60mil (±1.2mil)	1.52mm × 1.52mm (±0.030mm)
Thickness	12mil ± 1mil	0.300mm ± 0.025mm
Active area	52.76mil × 52.76mil ± 0.5mil	1.34mm × 1.34mm ± 0.013mm
Pad size	5.6mil ± 0.2mil	0.140mm ± 0.005mm

• Electrical Characteristics(T= 25℃)

Parameter	Symbol	Min	Type	Max	Unit	Test Conditions
Reverse Breakdown Voltage	V_{BR}	30	-	-	V	$I_R = 100\mu A$, $H=0$
Forward Voltage	V_F	-	-	1.3	V	$I_F = 10mA$, $H=0$
Reverse Dark Current	I_D	-	-	10	nA	$V_R = 10V$, $H=0$
Light Current	I_L	-	60	-	uA	$V_R = 10V$, $1mw/cm^2@940nm$
Peak Sensing Wavelength	λ_p	-	940	-	nm	-
Spectrum Sensitivity	λ	430	-	1100	nm	-
Junction Capacitance	C_j	-	15	-	pF	$V_R=3.5V$, $F=1\text{ MHz}$, $H=0$

• Spectral Response



• Outline dimension (mil)

